

SIEMENS

IL440

TRIAC PREDRIVER NON-ZERO CROSSING OPTOCOUPLER

FEATURES

- 600 V Blocking Voltage
- 7 mA Maximum Trigger Current
- Isolation Voltage, 3750 VAC, t=1 sec.
- Isolation Materials per UL94

APPLICATIONS

- High Current Triac Driver
- Solid State Relays
- Switch Small AC Loads

DESCRIPTION

The IL440 consists of a GaAs infrared emitter optically coupled to a silicon planar triac chip with a non-zero crossing network. The two semiconductors are assembled in a 6 pin dual-in-line plastic package. The output detector is capable of blocking up to 600 volts which permits control of off-line voltages up to 240 VAC. The IL440 can handle currents up to 100 mA_{RMS}.

Maximum Ratings**Emitter**

| | |
|---------------------------------|-------|
| Reverse Voltage | 5 V |
| Forward Current | 60 mA |
| Surge Current (P.W.<10 μs)..... | 3 A |

| | |
|---------------------------|--------|
| Power Dissipation..... | 100 mW |
| Junction Temperature..... | 100 °C |

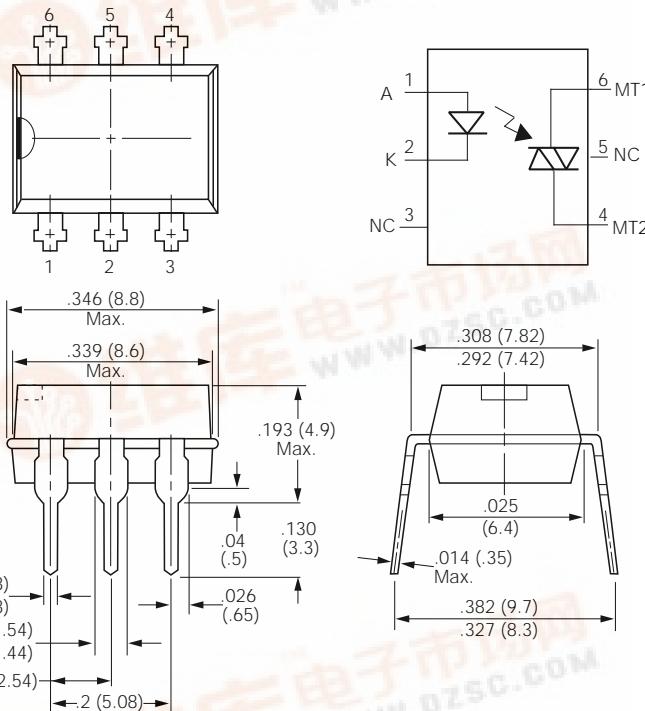
Detector

| | |
|---|--------|
| Peak Off-state Voltage..... | 600 V |
| On-state RMS Current | 100 mA |
| Peak Surge Current ($t_p \leq 10$ ms)..... | 1.2 A |
| Peak On-state Current..... | 2 A |
| Power Dissipation..... | 300 mW |
| Junction Temperature..... | 125 °C |

Package

| | |
|---|--|
| Isolation Voltage, 1 sec..... | 3750 VAC per Standard Climate 23°C/50% RH, DIN 50014 |
| Creepage | ≥7 mm |
| Clearance..... | ≥7 mm |
| Isolation Resistance | |
| $V_{IO}=500$ V, $T_A=25^\circ\text{C}$ | ≥ 10^{12} Ω |
| $V_{IO}=500$ V, $T_A=100^\circ\text{C}$ | ≥ 10^{11} Ω |
| Total Power Dissipation, $T_A=25^\circ\text{C}$ | 330 mW |
| Storage Temperature Range | -55°C to +125°C |
| Operating Temperature Range..... | -40°C to +100°C |
| Junction Temperature..... | 100°C |
| Lead Soldering Temperature (2 mm from case, $t < 10$ s.) | 260°C |

Package Dimensions in inches (mm)

**Maximum Safety Ratings**

This device is used for protective separation against electrical shock within the maximum safety ratings. This must be ensured by protective circuits in the applications.

| Parameter | Symbol | Max. | Unit | Test Condition |
|--------------------------------------|------------|------|------|---------------------------------------|
| Emitter | | | | |
| Forward Current | I_F | 130 | mA | |
| Detector | | | | |
| Power Dissipation | P_D | 300 | mW | $T_A \leq 25^\circ\text{C}$ |
| Coupled Device | | | | |
| Rated Impulse Voltage Sample Test | V_{IOTM} | 6 | kV | $t_{T1} = 10$ s, $t_{test} = 60$ s |

Electrical Characteristics, $T_A=25^\circ\text{C}$

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Test Condition |
|--|-----------------|------|------|------|------------------|--|
| Emitter | | | | | | |
| Forward Voltage | V_F | | 1.25 | 1.6 | V | $I_F=50 \text{ mA}$ |
| Breakdown Voltage | V_{BR} | 5 | | | V | $I_R=10 \mu\text{A}$ |
| Junction Capacitance | C_J | | 50 | | pF | $V_R=0 \text{ V}, f=1 \text{ MHz}$ |
| Detector | | | | | | |
| Off-state Output Terminal Voltage | V_{DRM} | 600 | | | V | $I_{DRM}=500 \text{ nA}$ |
| Peak On-state Voltage | V_{TM} | | 1.5 | 3 | V | $I_{TM}=100 \text{ mA}, I_{FT}=30 \text{ mA}$ |
| Critical Rate of Rise of Off-state Voltage | $(dv/dt)_{cr}$ | | 50 | | V/ μs | $I_F=0, V_S=240 \text{ V}_{\text{RMS}}$ |
| | $(dv/dt)_{crq}$ | 0.13 | 0.25 | | V/ μs | $I_F=30 \text{ mA}, V_S=60 \text{ V}_{\text{RMS}}$ |
| Coupled Device | | | | | | |
| Input Trigger Current | I_{FT} | | 5 | 7 | mA | $V_T=6 \text{ V}, R_L=150 \Omega$ |
| Holding Current | I_H | | | 1 | mA | $I_F \geq 10 \text{ mA}, V_S \geq 3 \text{ V}$ |